

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known	
	Application Number	10/624,959		
	Filing Date	July 22, 2003		
	First Named Inventor	Karen K. Gleason		
	Art Unit	1711		
	Examiner Name	Not Yet Assigned		
Sheet	1	of	1	Attorney Docket Number 101328-180

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	CW	2002/0042657 A1	04/11/2002	Pugh et al.	
	CX	2002/0062782 A1	05/30/2002	Norris et al.	
	CY	5,852,088	12/22/1998	Dismukes et al.	
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	DB	6,413,882 B1	07/02/2002	Leung et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†
		Country Code ² -Number ³ -Kind Code ⁴ (if known)				
	DC	WO 01/86038 A2	11/15/2001	Universidad Politecnica De Valencia et al.		
	DD	WO 01/96635 A2	12/20/2001	Merck Patent GMBH		

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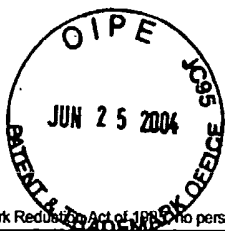
NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
	DG	Lanata, M. et al. "Titania Inverse Opals For Infrared Optical Applications" Optical Materials, Vol. 17, pps. 11-14 (2001);		
	DH	Yan, Hongwei et al. "Influence of Processing Conditions On Structures of 3D Ordered Macroporous Metals Prepared by Colloidal Crystal Templating" Chem. Mater., Vol. 13, pps. 4314-4321 (2001)		

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Examiner Signature		Date Considered	11/04
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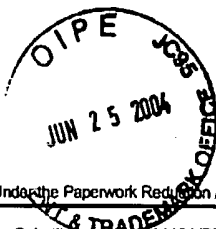
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/624,959 (Conf #6293)
				Filing Date	July 22, 2003
				First Named Inventor	Karen K. Gleason
				Art Unit	Not Yet Assigned
				Examiner Name	Not Yet Assigned
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		Country-Number				
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	BB	EP 1 148 539 A2	10/24/2001	Applied Materials, Inc.		
	BC	EP 1 195 451 A1	04/10/2002	Applied Materials, Inc.		
MF	BD	WO 03/005429 A1	01/16/2003	Postech Foundation		



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		Filing Date	July 22, 2003
		First Named Inventor	Karen K. Gleason
		Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet	2	of	3
		Attorney Docket Number	101328-180

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MF	CA	Baklanov, M.R. et al. "Comparative Study of Porous SOG Films With Different Non-Destructive Instrumentation," IEEE pp. 189-191, (2001);	
	CB	Barklanov, M.R. "Determination of Pore Size Distribution In Thin Films By Ellipsometric Porosimetry" J. Vac. Sci. Technol. B., Vol. 18, No. 3, pp. 1385-13981, (2000);	
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	CO	Sanchez, M.I. et al. "Nanofoam Porosity By Infrared Spectroscopy," Journal of Polymer Science: Part B: Polymer Physics, Vol. 33, pp. 253-257 (1995);	
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Examiner Signature		<i>[Signature]</i>	Date Considered 10/04

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